

650V 360mohm Super-Junction Power MOSFET
AK3S65N3K6KMF

Description:

This SJ device provides good FOM performance, better EMI for customer application.

Features:

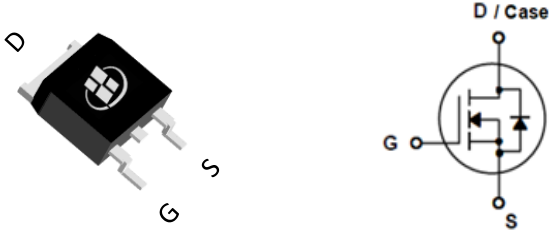
- EMI-Friendly
- RoHS compliant
- Halogen-free

Applications:

- High Frequency Switching
- Quick Charging and Adapter

Key Performance Parameters:

Parameter	Value	Unit
V_{DS}	650	V
$R_{DS(on), max} @V_{GS} = 10\text{ V}$	360	mΩ
I_D	12.5	A



Ordering Information:

Ordering Code	Package Type	Marking Code	Form	Packing
AK3S65N3K6KMF	TO-252	3S65N3K6KMF	Tape Reel	See the detail package information

Maximum Ratings (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{DS}	Drain - Source Voltage	650	V
I _D	Drain Current - Continuous (T _C = 25°C) ^(Note 1)	12.5	A
	Drain Current - Continuous (T _C = 100°C)	7.5	A
I _{DM}	Drain Current - Pulsed ^(Note 2)	34	A
V _{GS}	Gate - Source Voltage	± 30	V
E _{AS}	Single Pulsed Avalanche Energy ^(Note 3)	54	mJ
P _D	Power Dissipation (T _C = 25°C)	75.5	W
dV/dT	MOSFET dv/dt ruggedness, V _{DS} = 0...480 V	50	V/ns
	Reverse diode dv/dt, V _{DS} = 0...480 V	50	V/ns
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C

Thermal Characteristics

Symbol	Parameter	Value	Units
R _{θJC}	Thermal Resistance, Junction - to - Case, Steady State	1.65	°C/W
R _{θJA}	Thermal Resistance, Junction - to - Ambient, Steady State ^(Note 4)	60	°C/W

Notes:

1. The max drain current rating limited by maximum junction temperature
2. Repetitive Rating: Pulse width limited by maximum junction temperature
3. L = 75 mH, V_{DD} = 100 V, I_{AS} = 1.2 A, R_G = 50 Ω, Starting T_J = 25 °C
4. Mount on minimum PCB layout

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Static Characteristics						
V _{(BR)DSS}	Drain - Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	650			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 650 V, V _{GS} = 0 V			10	μA
I _{GSS}	Gate Leakage Current	V _{GS} = ± 30 V, V _{DS} = 0 V			±100	nA
V _{GS(th)}	Gate Threshold voltage	V _{DS} = V _{GS} , I _D = 250 μA	2.5	3.4	4.5	V
R _{DS(ON)}	Drain - Source on - state resistance	V _{GS} = 10 V, I _D = 5 A		302	360	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 400 V, V _{GS} = 0 V, f = 1 MHz		530		pF
C _{oss}	Output Capacitance			15		pF
C _{rss}	Reverse Transfer Capacitance			5.5		pF
C _{o(er)}	Effective output capacitance, energy related	V _{DS} = 0...400 V, V _{GS} = 0 V		27		pF
C _{o(tr)}	Effective output capacitance, time related	V _{DS} = 0...400 V, V _{GS} = 0 V, I _D =constant		195		pF
R _g	Gate Resistance	f = 1 MHz		16		Ω
Switching Characteristics						
t _{d(on)}	Turn On Delay Time	V _{DD} = 400 V , I _D = 5 A, V _{GS} = 10 V, R _G = 5 Ω		52		ns
t _r	Rise Time			7		ns
t _{d(off)}	Turn Off Delay Time			37		ns
t _f	Fall Time			10		ns
Q _g	Total Gate Charge	V _{DD} = 480 V , I _D = 12.5 A, V _{GS} = 10 V		20		nC
Q _{gs}	Gate - Source Charge			4		nC
Q _{gd}	Gate - Drain Charge			11		nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Body - Diode Forward Current				12.5	A
I _{SM}	Maximum Pulsed Body - Diode Forward Current				34	A
V _{SD}	Diode Forward Voltage	V _{GS} = 0 V, I _S = 5 A		1.05		V
t _{rr}	Reverse recovery time	V _{DD} = 400 V, I _D = 5 A, di/dt = 100 A/μs		59		ns
Q _{rr}	Reverse recovery charge			0.35		μC
I _{rrm}	Peak Reverse Recovery Current			13		A

Electrical Characteristics Diagrams

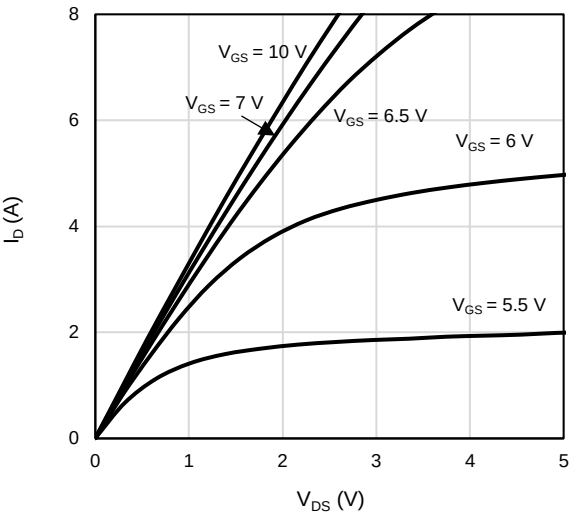


Figure 1: On-Region Characteristics

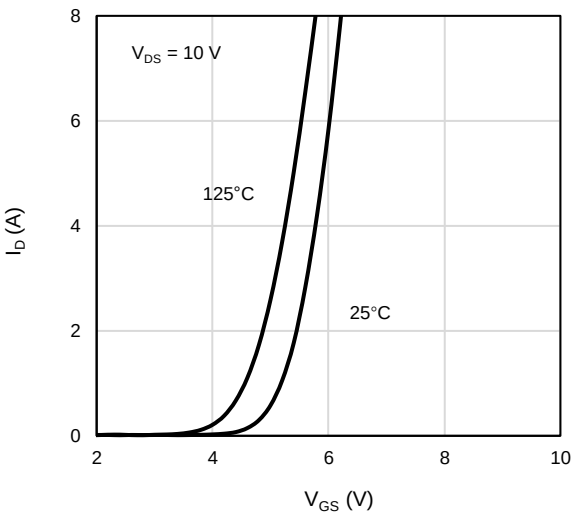


Figure 2: Transfer Characteristics

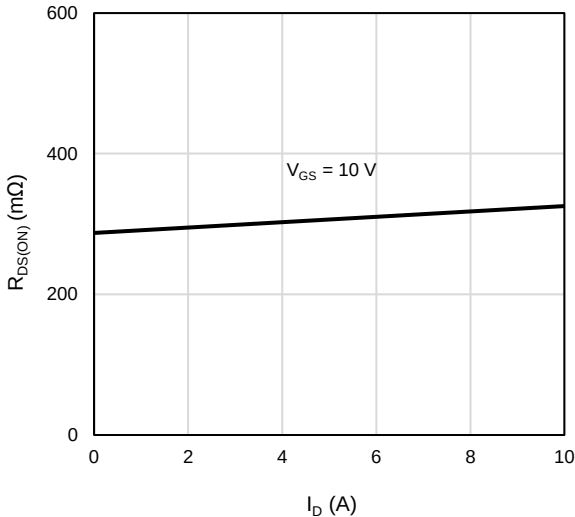


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

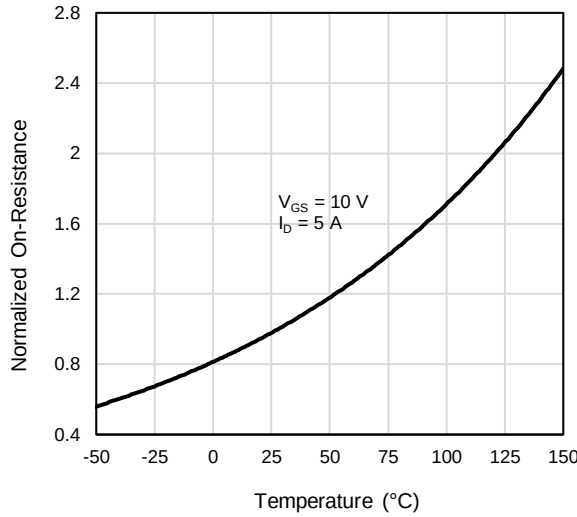


Figure 4: On-Resistance vs. Junction Temperature

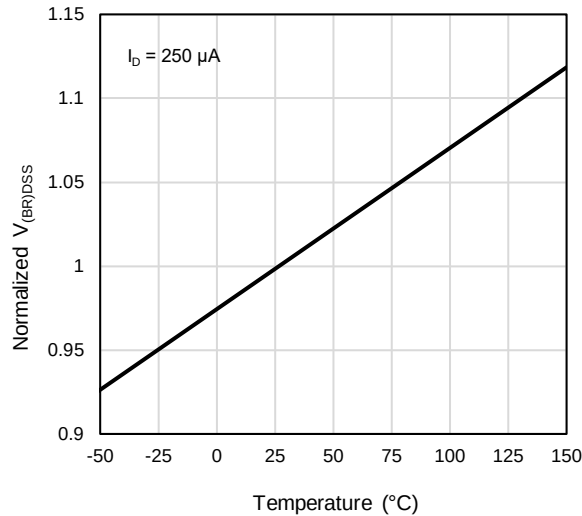


Figure 5: Breakdown Voltage vs. Junction Temperature

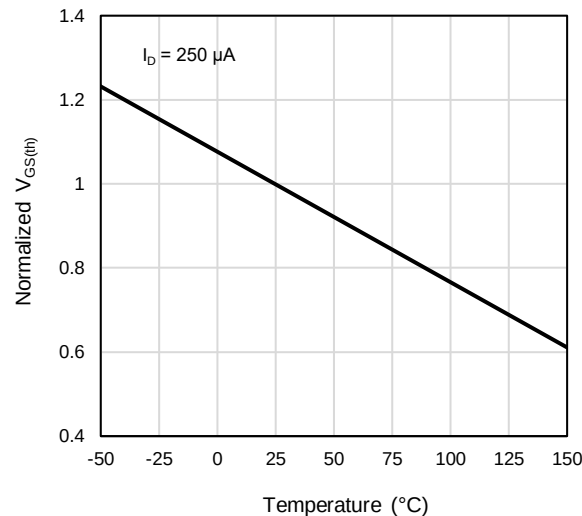
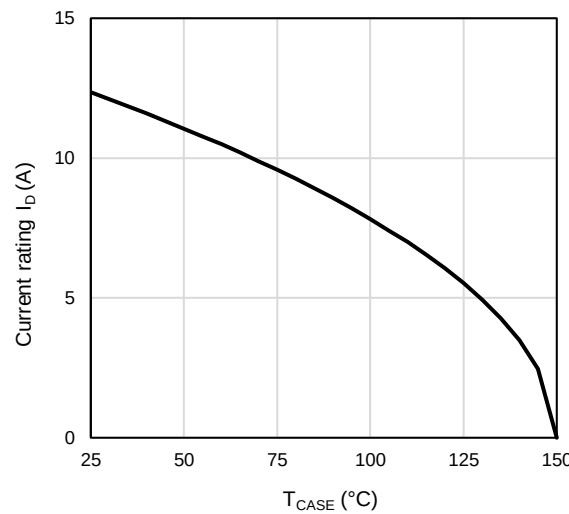
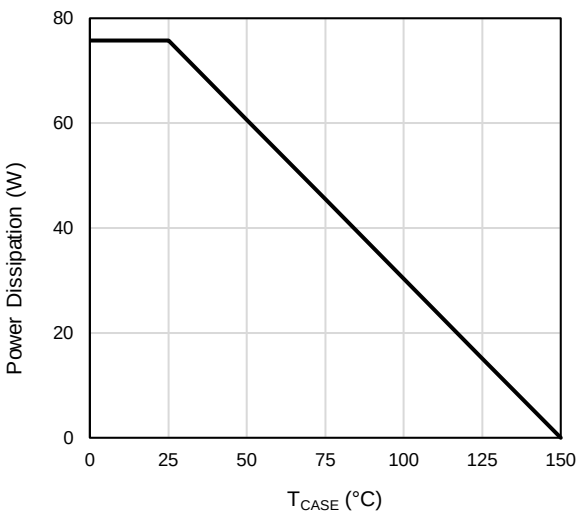
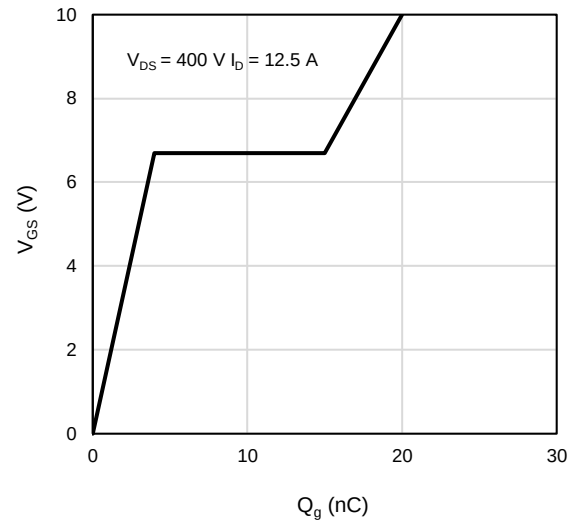
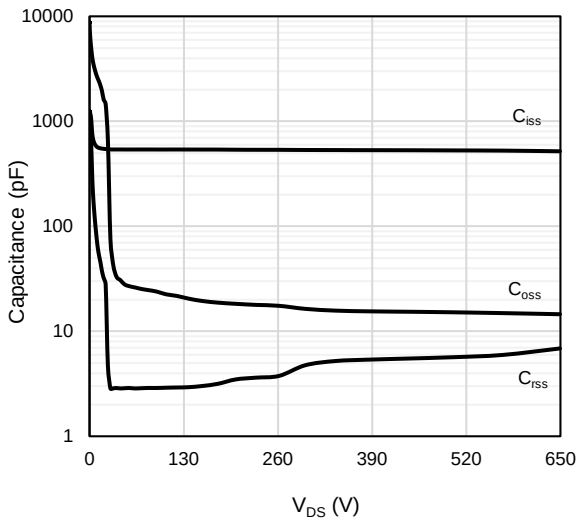
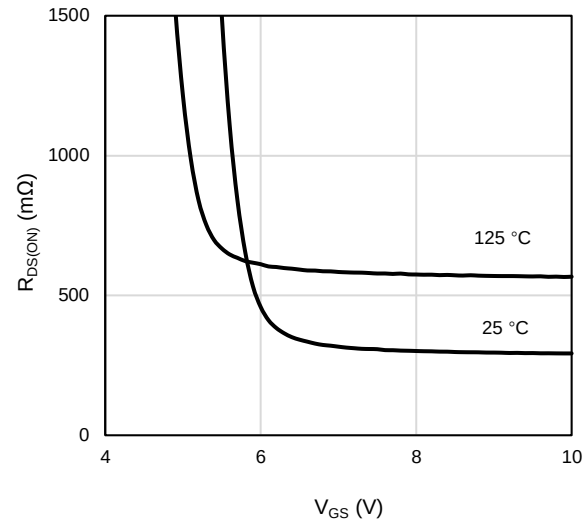
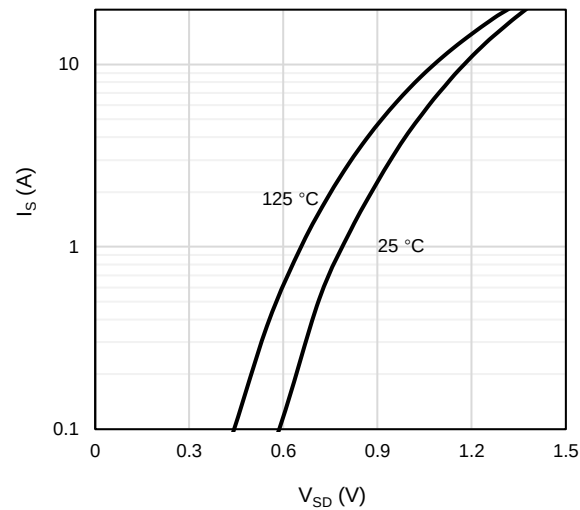


Figure 6: Threshold Voltage vs. Junction Temperature



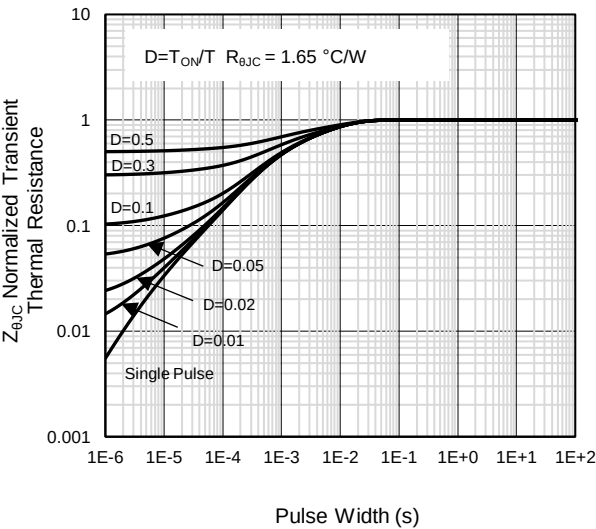


Figure 13: Normalized Maximum Transient Thermal Impedance

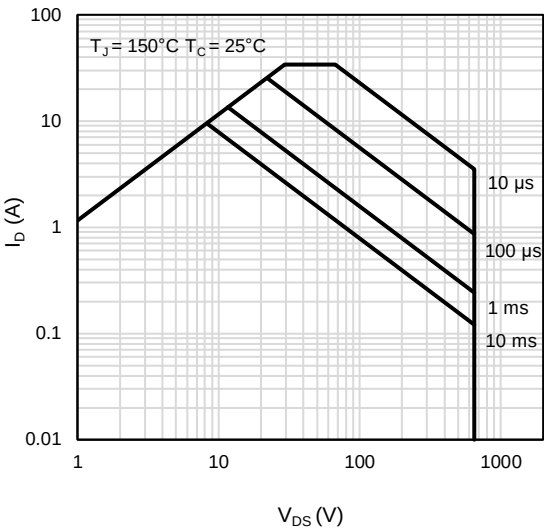
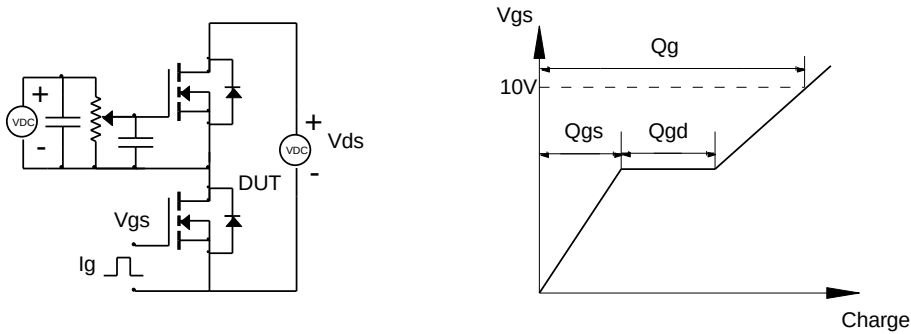


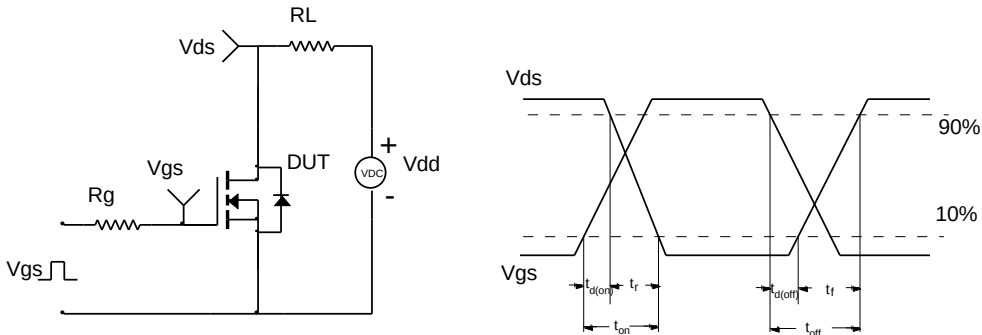
Figure 14: Maximum Forward Biased Safe Operating Area

Test Circuit and Waveform

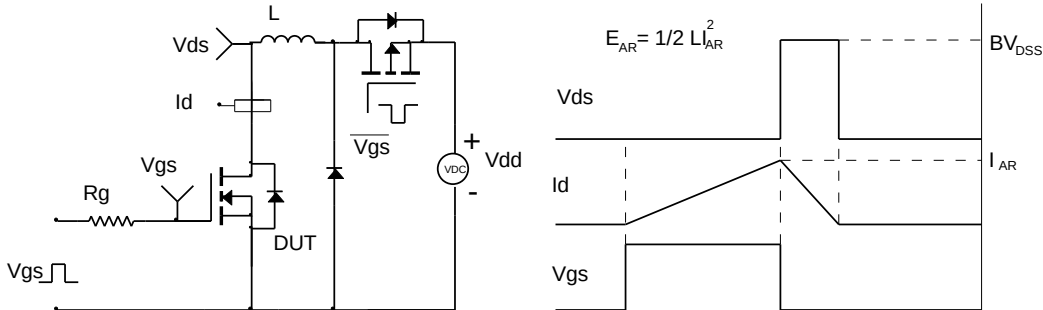
Gate Charge Test Circuit & Waveform



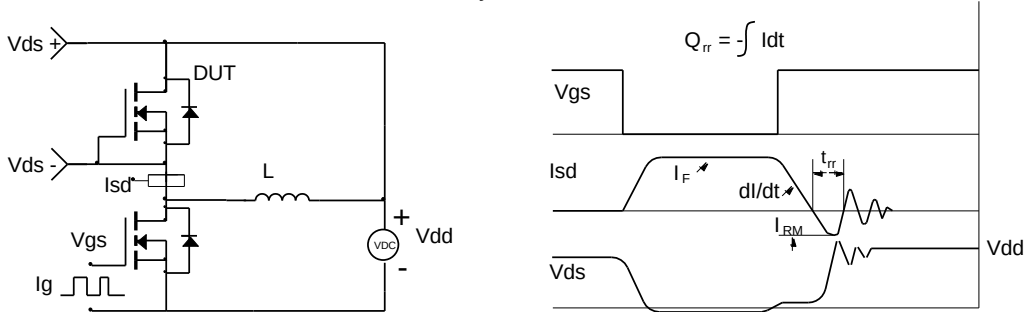
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Revision History

Revision	Released	Remark
Rev.1.0	2025	Initial Release

Disclaimer

The information given in this document describes the independent performance of the product, but similar performance is not guaranteed under other working conditions, and cannot be guaranteed when installed with other products or equipment. To achieve the required performance of the product in actual scenarios, the customer should conduct a complete application test to assess the functionality of the product.

Alkaidsemi assumes no responsibility for equipment failures result from using products at values that exceed the ratings, operating conditions, or other parameters listed in the product specifications.

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